



CHINA BASE
INTERNATIONAL

SOT-523



DAN217T

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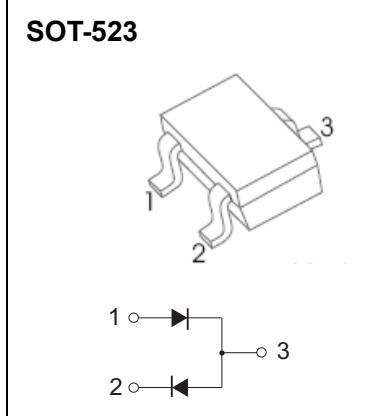
Plastic-Encapsulate Diode

SWITCHING DIODE

FEATURES

- Small surface mounting type
- Two diode elements are connected in series

MARKING:BA1



Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	80	V
DC Blocking Voltage	V _R	80	V
Forward Continuous Current	I _{FM}	300	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I _{FSM}	2.0	A
Average Rectified Output Current	I _O	100	mA
Power Dissipation	P _D	200	mW
Thermal resistance From Junction to ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 100μA	80		V
Reversen voltage leakage current	I _R	V _R =70V		0.2	μA
Forward voltage	V _F	I _F =100mA		1.2	V



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Typical Characteristics

